

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IPD60R360P7,IIPD60R360P7

• FEATURES

- Static drain-source on-resistance: $R_{\text{DS}}(\text{on}){\leqslant}0.36\Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

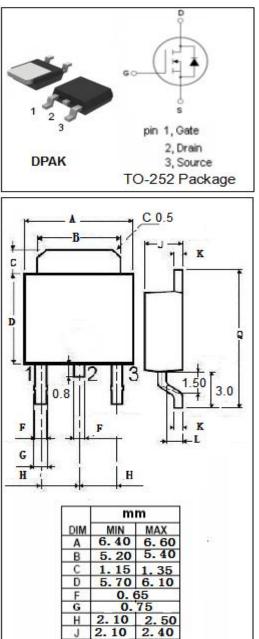
Suitable for hard and soft switching

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

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SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	600	V				
V _{GS}	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous 9		А				
I _{DM}	Drain Current-Single Pulsed	26	А				
P _D	Total Dissipation @T _c =25°C 41		W				
Tj	Max. Operating Junction Temperature 150		°C				
T _{stg}	Storage Temperature	-40~150	°C				

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
Rth(j-c)	Channel-to-case thermal resistance	3.04	°C/W	
Rth(j-a)	Rth(j-a) Channel-to-ambient thermal resistance		°C/W	



K

0

0.40

0.90

9.90

0.60

10

10



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	600			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =0.14mA	3		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =2.7A			0.36	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μA
V _{SD}	Diode forward voltage	I _F =2.7A, V _{GS} = 0V		0.9		V

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